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(54) Title: **CLEANING GAS FOR SEMICONDUCTOR PRODUCTION EQUIPMENT**

(57) Abstract: The present invention relates to (1) a cleaning gas for cleaning semiconductor production equipment, obtained by mixing SF₆ and one or both of F₂ with and NF₃ with an inert gas at a specific ratio; (2) a cleaning gas for cleaning semiconductor production equipment, obtained by mixing SF₆ and one or both of F₂ and NF₃ with an inert gas and an oxygen-containing gas at a specific ratio; (3) a method for cleaning semiconductor production equipment using the gas; and (4) a method for producing a semiconductor device including a cleaning step using the cleaning gas. By using the cleaning gas for semiconductor production equipment of the present invention which is high in the etching rate, efficient cleaning and production of semiconductor production equipment with excellent cost performance can be achieved.

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